

Evaluation of the Low Resistance Strip Sensors Fabricated at CNM

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Results from the second batch of Low-R strip sensors fabricated at CNM-Barcelona will be presented. This second batch implements several technological and design changes in order to correct the PTP structure, not fully functional in the first batch. The tests on the newly fabricated sensors show good general performance plus a correct behaviour of the PTP structure. The results from the laser tests show the proper limitation on the strip voltage in the event of a beam-loss even when the change injection is produced far from the PTP structure for the Low-R strip sensors. This strip voltage limitation is not seen for the standard sensors also fabricated in the same wafer. This demonstrates the effectiveness of the proposed low resistance strip. Finally, alternative technological implementations for the Low-R sensors will be presented. These solutions are in fabrication at the moment at CNM.

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